

**SMPS MOSFET**

**IRF7467**

**Applications**

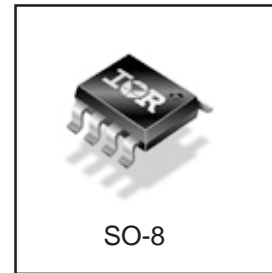
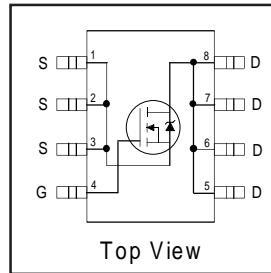
- High Frequency DC-DC Isolated Converters with Synchronous Rectification for Telecom and Industrial use
- High Frequency Buck Converters for Computer Processor Power

HEXFET® Power MOSFET

$V_{DS}$	$R_{DS(on)}$ max	$I_D$
30V	12m $\Omega$	11A

**Benefits**

- Ultra-Low Gate Impedance
- Very Low  $R_{DS(on)}$  at 4.5V  $V_{GS}$
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	11	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	9.0	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	90	
$P_D @ T_A = 25^\circ\text{C}$	Maximum Power Dissipation	2.5	W
$P_D @ T_A = 70^\circ\text{C}$	Maximum Power Dissipation	1.6	W
	Linear Derating Factor	0.02	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	$^\circ\text{C}$

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient <sup>④</sup>	—	50	

Notes ① through ④ are on page 8  
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## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	9.4	12	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A ③
		—	10.6	13.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 9.0A ③
		—	17	35		V <sub>GS</sub> = 2.8V, I <sub>D</sub> = 5.5A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	0.6	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
		—	—	100		V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 12V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -12V

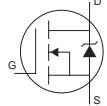
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	28	—	—	S	V <sub>DS</sub> = 16V, I <sub>D</sub> = 9.0A
Q <sub>g</sub>	Total Gate Charge	—	21	32	nC	I <sub>D</sub> = 9.0A
Q <sub>gs</sub>	Gate-to-Source Charge	—	6.7	10		V <sub>DS</sub> = 15V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	5.8	8.7		V <sub>GS</sub> = 4.5V ③
Q <sub>oss</sub>	Output Gate Charge	—	21	29		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V
t <sub>d(on)</sub>	Turn-On Delay Time	—	7.8	—		ns
t <sub>r</sub>	Rise Time	—	2.5	—	R <sub>G</sub> = 1.8Ω	
t <sub>d(off)</sub>	Turn-Off Delay Time	—	19	—	V <sub>GS</sub> = 4.5V ③	
t <sub>f</sub>	Fall Time	—	4.0	—		
C <sub>iss</sub>	Input Capacitance	—	2530	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	706	—		V <sub>DS</sub> = 15V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	46	—		f = 1.0MHz

## Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	223	mJ
I <sub>AR</sub>	Avalanche Current①	—	11	A

## Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	90		
V <sub>SD</sub>	Diode Forward Voltage	—	0.79	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 9.0A, V <sub>GS</sub> = 0V ③
		—	0.65	—		T <sub>J</sub> = 125°C, I <sub>S</sub> = 9.0A, V <sub>GS</sub> = 0V
t <sub>rr</sub>	Reverse Recovery Time	—	40	60	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 9.0A, V <sub>R</sub> = 15V
Q <sub>rr</sub>	Reverse Recovery Charge	—	56	84		di/dt = 100A/μs ③
t <sub>rr</sub>	Reverse Recovery Time	—	43	65	ns	T <sub>J</sub> = 125°C, I <sub>F</sub> = 9.0A, V <sub>R</sub> = 15V
Q <sub>rr</sub>	Reverse Recovery Charge	—	64	96		di/dt = 100A/μs ③

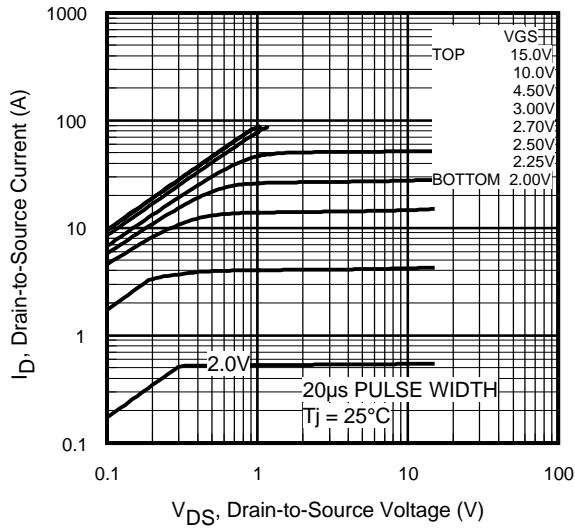


Fig 1. Typical Output Characteristics

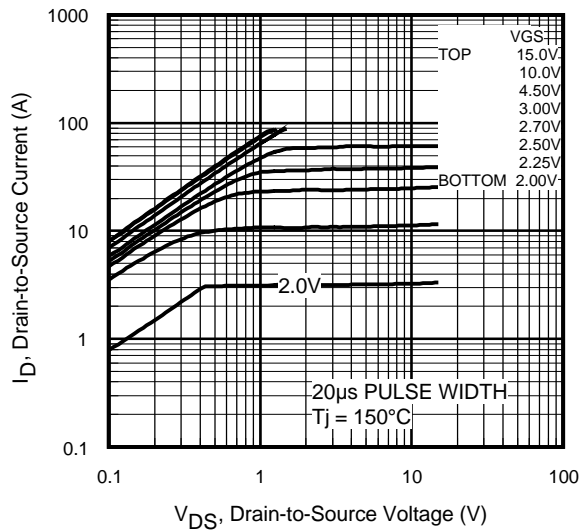


Fig 2. Typical Output Characteristics

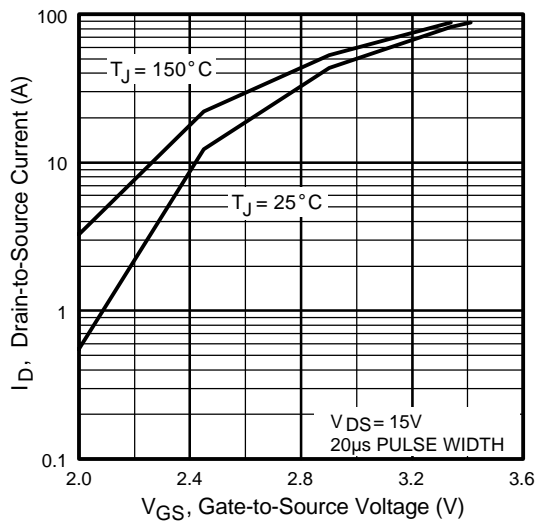


Fig 3. Typical Transfer Characteristics

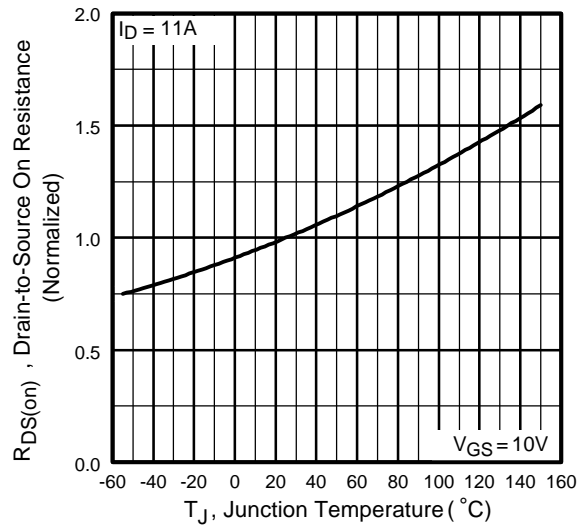
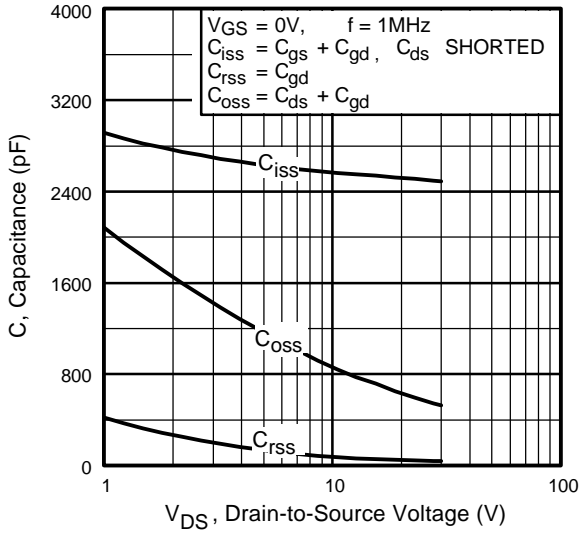
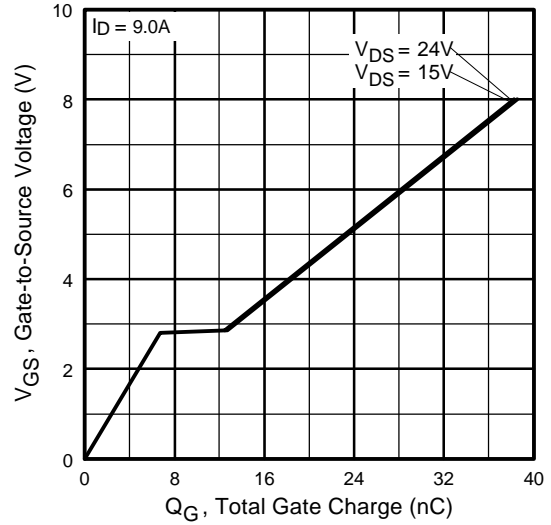


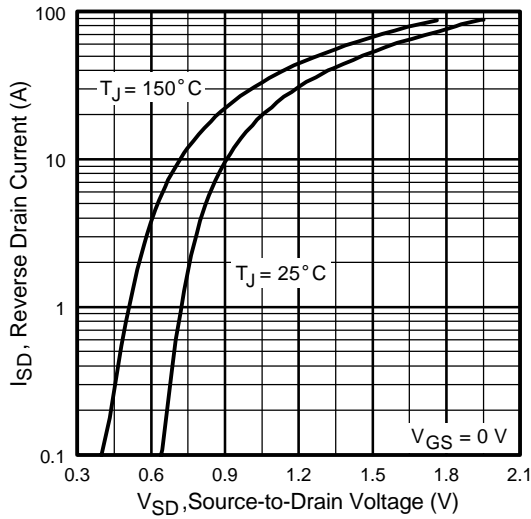
Fig 4. Normalized On-Resistance Vs. Temperature



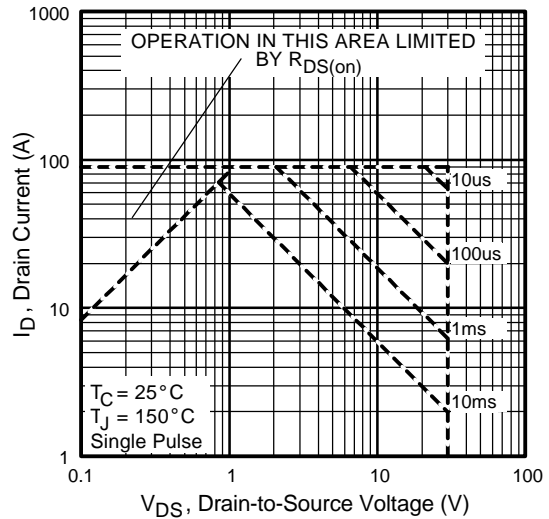
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



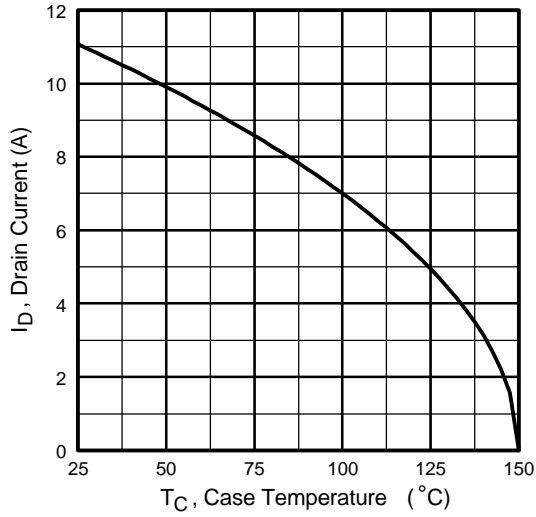
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



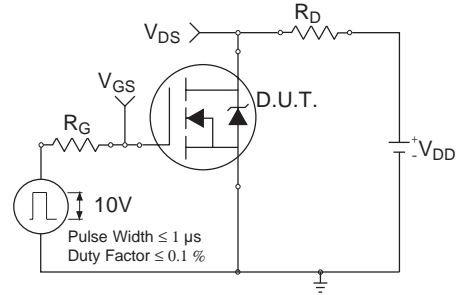
**Fig 7.** Typical Source-Drain Diode Forward Voltage



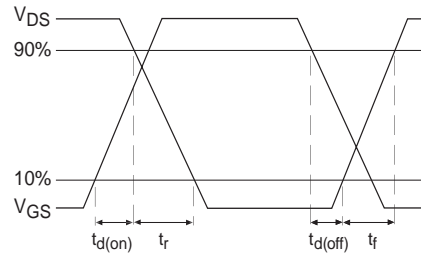
**Fig 8.** Maximum Safe Operating Area



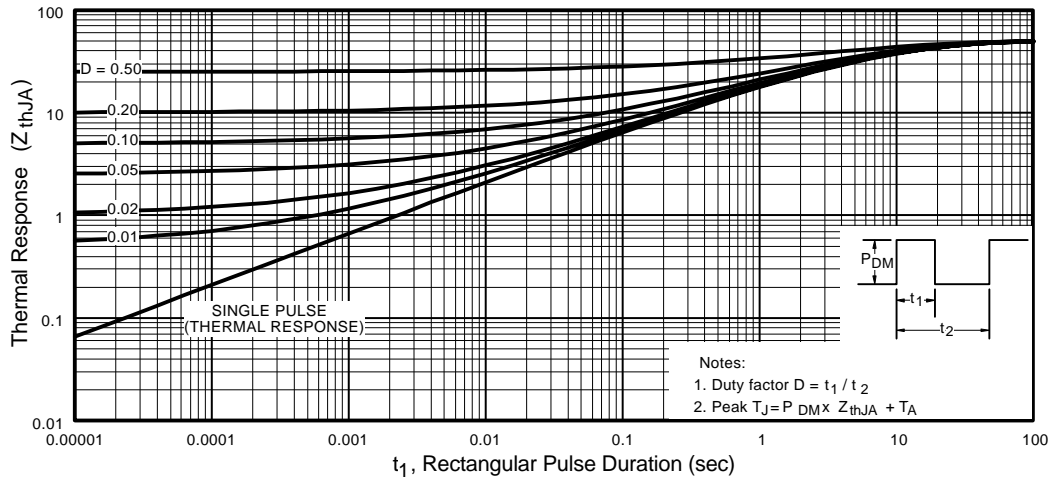
**Fig 9.** Maximum Drain Current Vs. Case Temperature



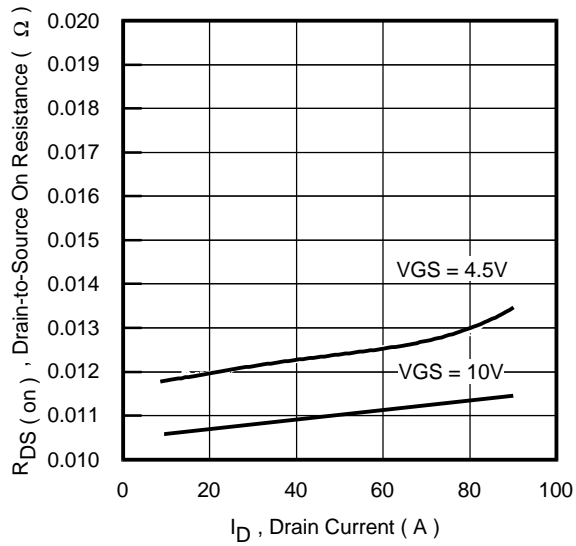
**Fig 10a.** Switching Time Test Circuit



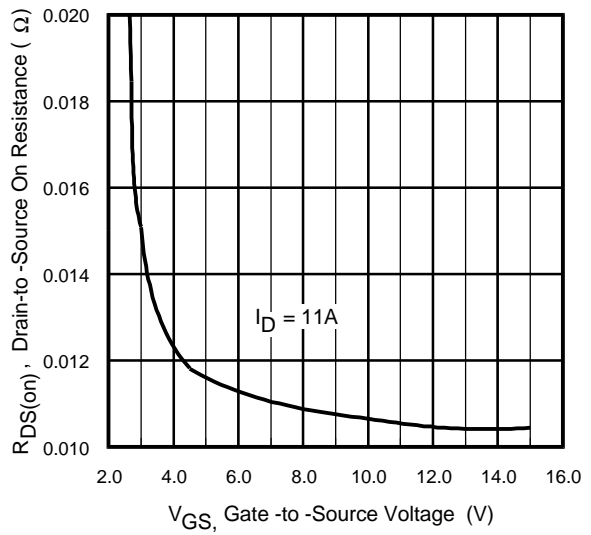
**Fig 10b.** Switching Time Waveforms



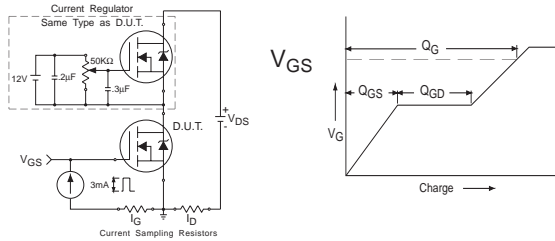
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



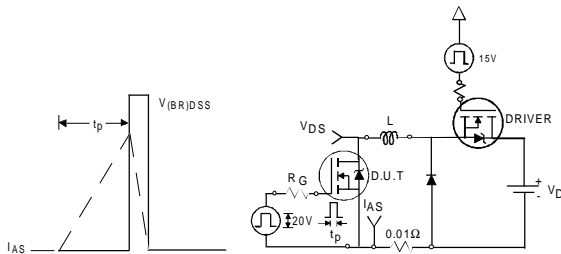
**Fig 12.** On-Resistance Vs. Drain Current



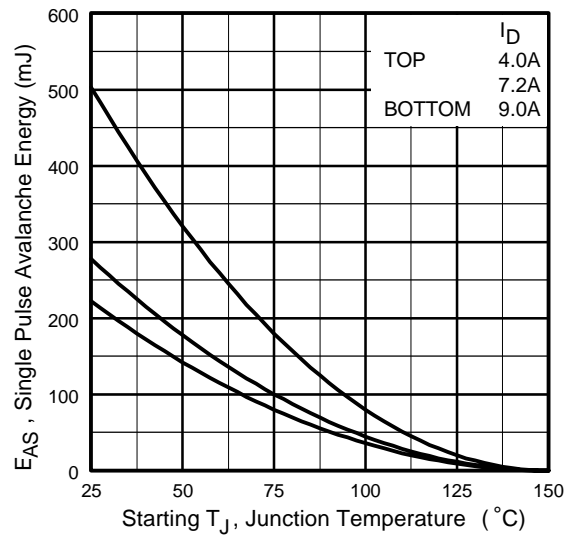
**Fig 13.** On-Resistance Vs. Gate Voltage



**Fig 14a&b.** Basic Gate Charge Test Circuit and Waveform

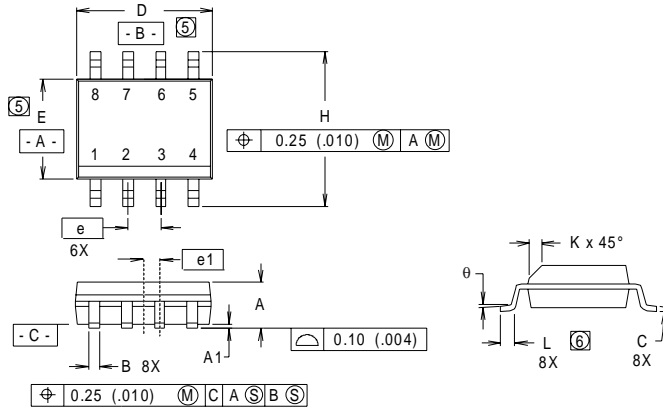


**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms



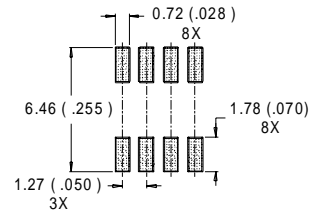
**Fig 15c.** Maximum Avalanche Energy Vs. Drain Current

## SO-8 Package Details



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
$\theta$	0°	8°	0°	8°

RECOMMENDED FOOTPRINT

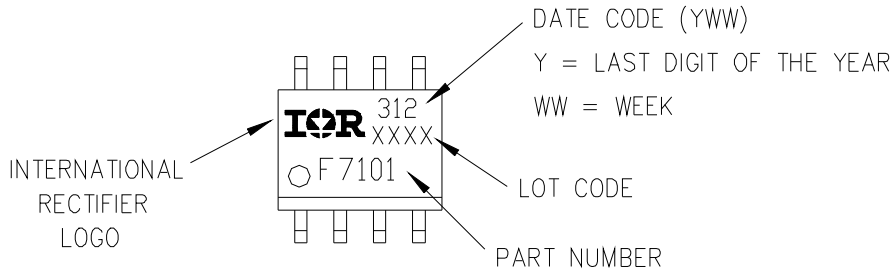


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS  
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
- ⑥ DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

## SO-8 Part Marking

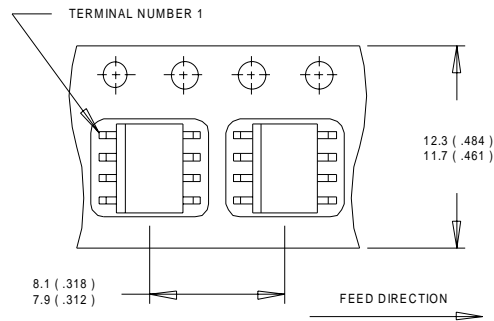
EXAMPLE: THIS IS AN IRF7101



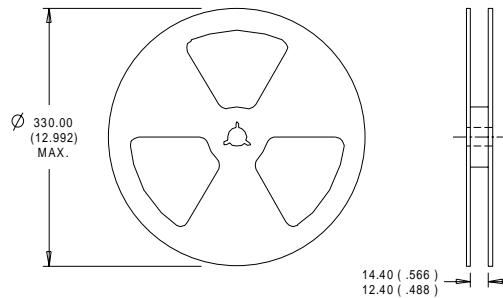
# IRF7467

International  
**IR** Rectifier

## SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 5.5\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 9.0\text{A}$ .
- ③ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board,  $t < 10$  sec

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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